

SD101AWS

THRU

SD101CWS

Features

- Low Reverse Recovery Time
- Low Reverse Capacitance
- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection

Mechanical Data

- Case: SOD-323 plastic case
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: Indicated by Cathode Band

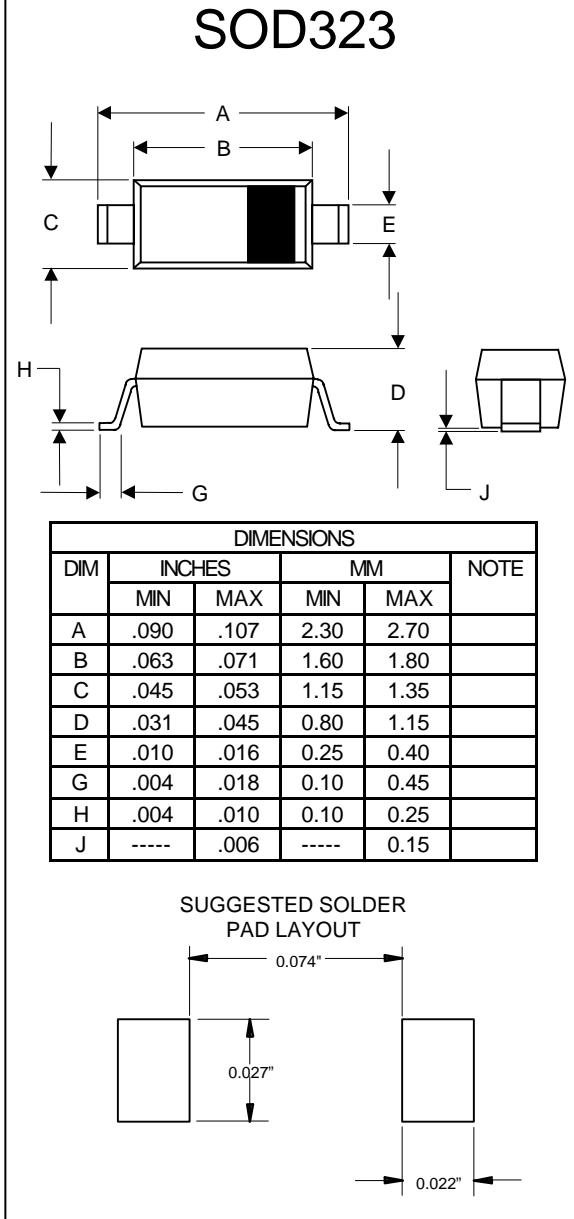
Maximum Ratings @ 25°C Unless Otherwise Specified

Characteristic	Symbol	SD101AWS	SD101BWS	SD101CWS
Peak Repetitive Reverse Voltage	V_{RRM}			
Working Peak Reverse Voltage	V_{RWM}	60V	50V	40V
DC Blocking Voltage	V_R			
RMS Reverse Voltage	$V_{R(RMS)}$	42V	35V	28V
Maximum single cycle surge 10us square wave	I_{FSM}		2.0A	
Power Dissipation(Note 1)	P_d		400mW	
Thermal Resistance, Junction to Ambient	R		650°C/W	
Junction Temperature	T_j		125°C	
Operation/Storage Temp. Range	T_{STG}		-55 to +150°C	

Electrical Characteristics @ 25°C Unless Otherwise Specified

Characteristic	Symbol	Max	Test Condition
Leakage Current	I_R	200nA	$V_R=50V$
SD101AWS		200nA	$V_R=40V$
SD101BWS		200nA	$V_R=30V$
Maximum Forward Voltage Drop	V_F	0.41V	
SD101AWS		0.4V	
SD101BWS		.39V	$I_F=1mA$
SD101CWS		1V	$I_F=15mA$
SD101AWS		0.95V	
SD101BWS		0.9V	
Junction Cap.	C_j	2.0pF	$V_R=0V, f=1.0MHz$
SD101AWS		2.1pF	
SD101BWS		2.2pF	
SD101CWS			
Reverse Recovery Time	t_{rr}	1ns	$I_F=I_R=5mA$, recover to 0.1 I_R

Small Signal Schottky Diodes



Note: 1. Valid provided that electrodes are kept at ambient temperature

SD101AWS thru SD101CWS

Figure 1. Typical variation of forward current vs.fwd. Voltage for primary conduction through the schottky barrier

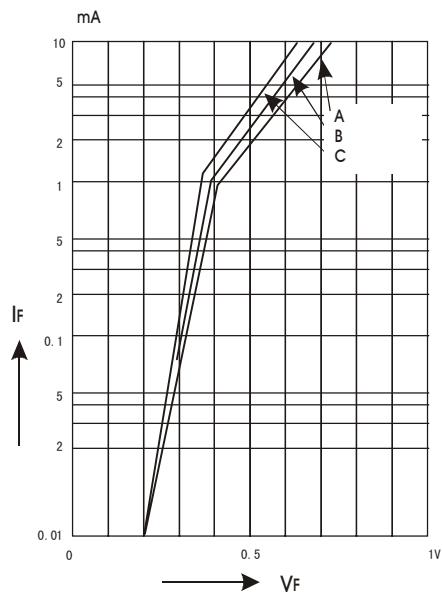


Figure 3.Typical variation of reverse current at versus temperature

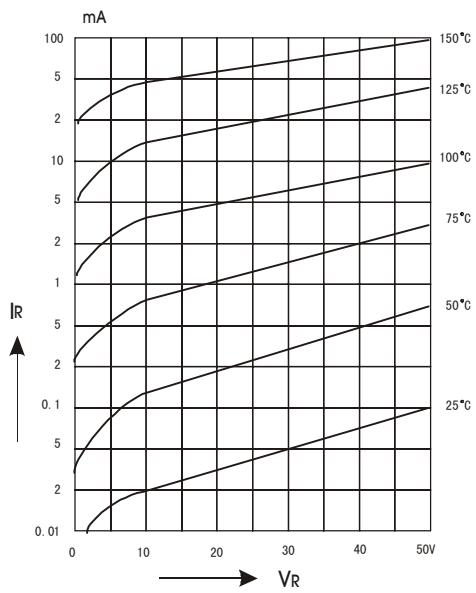


Figure 2. Typical forward conduction curve of combination Schottky barrier and PN junction guard ring

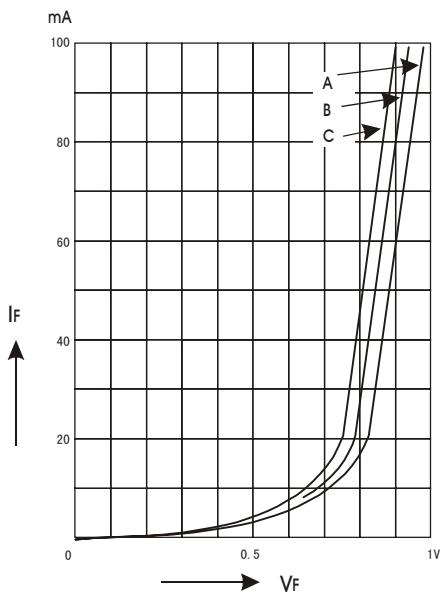


Figure 4. Typical capacitance curve as a function of reverse voltage

